







• 0.18µ CMOS	TABLE I 0.18-µm Process Features	
 25.4 million transistors 6 metal layers	Layer	Pitch
• Flip-chip with 1014 pads Recall that the Alpha had 21264 had 15.2 million transistors	Poly	0.48µm
	Metal 1	0.60µm
	Metal 2	0.72µm
	Metal 3	0.72µm
	Metal 4	1.45µm
	Metal 5	1.80µm
	Metal 6	2.00µm















Reducing Wire Delay of Long Wires

Can reduce wire delay by making wire wider if fringing capacitance dominates wire capacitance.

If substrate capacitance dominates, then increasing width decreases R, but also increases C by same amount so total RC remains the same.

Can also reduce wire delay by splitting a wire into segments and putting a buffer between each segments.









Inductance Affects Delay

Delay in Clock distribution metal H-tree network affected by R, C, and L.

For Ghz speed clocks in a metal distribution network, must include L in delay calculations

RLC and Return Path Extraction	Line Delay	Gate Delay
Addition of return path resistance	+ 27 %	- 3%
Addition of Inductance	+ 8 %	-10 %
Difference from RC Model	+ 35 %	- 13%



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Inductance adds extra delay in current return path Inductive effects decreased clock buffer delays dues to faster transition rates. BR 6/00























On-Die-Clock-Shrink Block

Because of Ghz clock rate, no tester able to accurately supply and manipulate clock edges if PLL bypassed.

Functional block called On-Die-Clock-Shrink (ODCS) block included for edge manipulation for post silicon debug.



